

L8107

EK0502-0022 Ver.A



PIN Diode

FEATURES

- High Power Handling
- High Zero Bias Impedance
- Low Capacitance
- High Parallel Resistance
- High Isolation
- Hermetic Ceramic MELF Package
- RoHS Compliant
- Pb Free

APPLICATIONS

- High power antenna switch

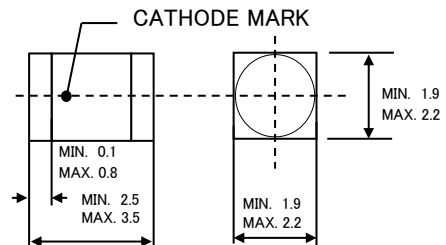
DIMENSIONS

Unit : mm

GENERAL DESCRIPTION

The L8107 PIN diode is designed for solid state antenna switching applications in mobile radios.

The L8107 PIN diode employs a square outline which makes it suitable for reflow assembly on surface mounting.



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	RATINGS	UNITS
VRM	Repetitive Peak Reverse Voltage	90	V
PD*	Power Dissipation	1	W
Tj	Junction Temperature	175	°C
Tstg	Storage Temperature Range	-55 to 175	°C

*) Mounting on glass epoxy PCB (50mm x 50mm x 1.6mm)

ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
IR	Reverse Current	VR = 50V	-	-	10	μA
VF	Forward Voltage	IF = 50mA	-	0.85	1.0	V
Ct	Diode Capacitance	VR = 40V, f = 100MHz	-	0.4	0.6	pF
Rfs	Forward Series Resistance	IF = 50mA, f = 100MHz	-	1.2	1.5	Ω
RP	Parallel Resistance	VR = 0V, f = 100MHz	7.0	10.0	-	kΩ

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■ TYPICAL PERFORMANCE CHARACTERISTICS

